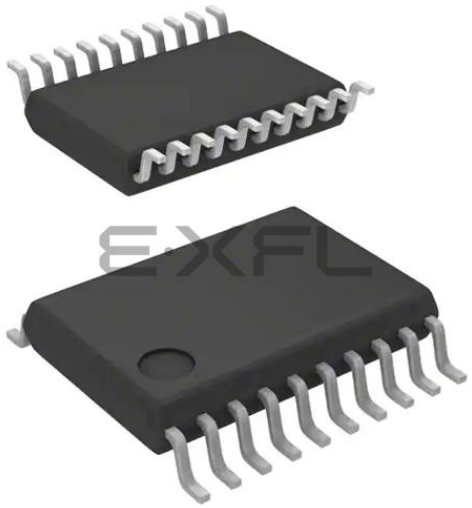
Renesas Electronics America Inc - R5F211A3SP#U0 Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, SIO, SSU, UART/USART
Peripherals	LED, POR, Voltage Detect, WDT
Number of I/O	13
Program Memory Size	12KB (12K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	768 x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 4x10b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-LSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f211a3sp-u0

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1. Overview

These MCUs are fabricated using the high-performance silicon gate CMOS process, embedding the R8C/Tiny Series CPU core, and is packaged in a 20-pin molded-plastic LSSOP, SDIP or a 28-pin plastic molded-HWQFN. It implements sophisticated instructions for a high level of instruction efficiency. With 1 Mbyte of address space, they are capable of executing instructions at high speed.
Furthermore, the R8C/1B Group has on-chip data flash ROM (1 KB × 2 blocks).
The difference between the R8C/1A Group and R8C/1B Group is only the presence or absence of data flash ROM. Their peripheral functions are the same.

1.1 Applications

Electric household appliances, office equipment, housing equipment (sensors, security systems), portable equipment, general industrial equipment, audio equipment, etc.

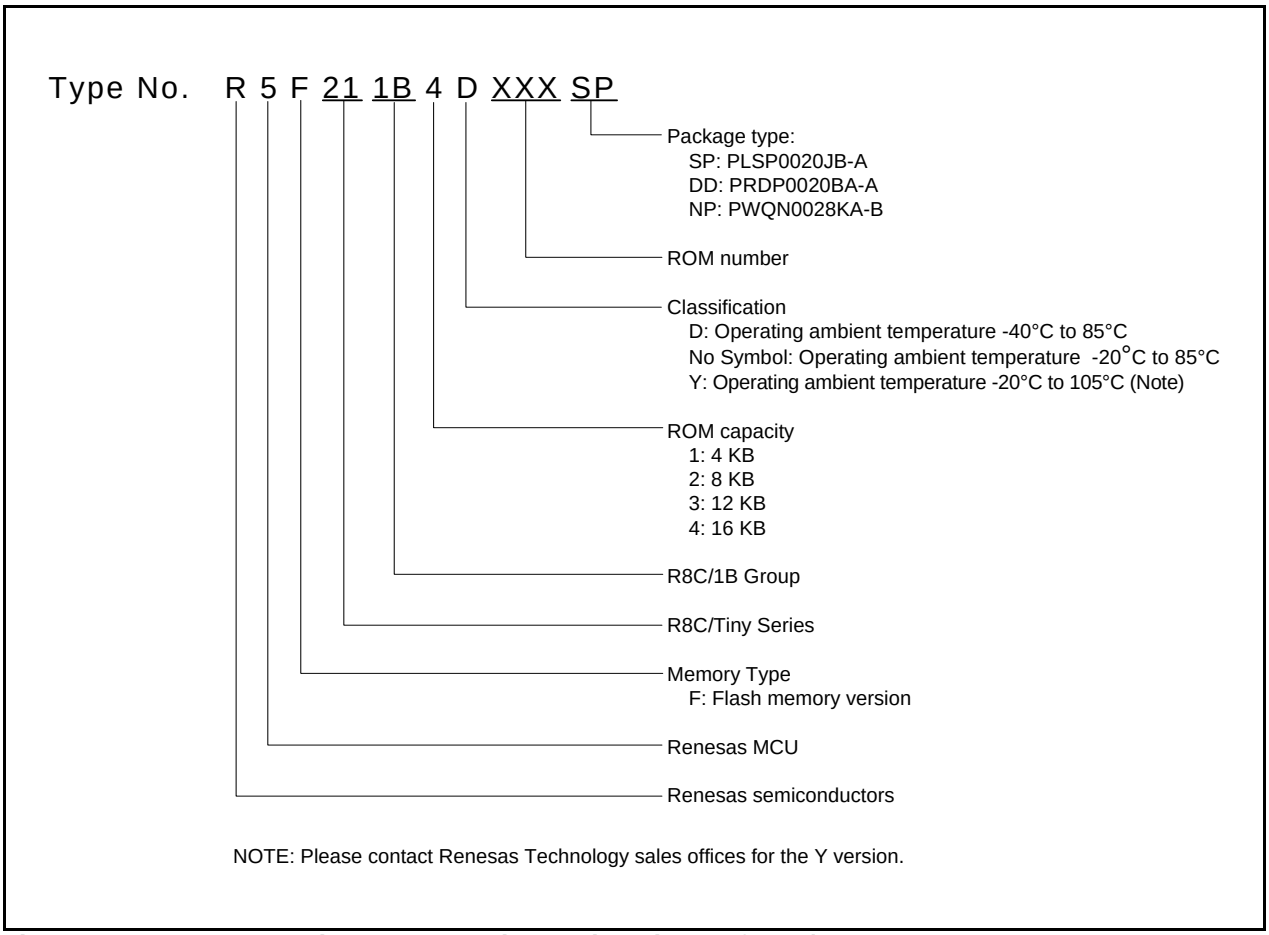


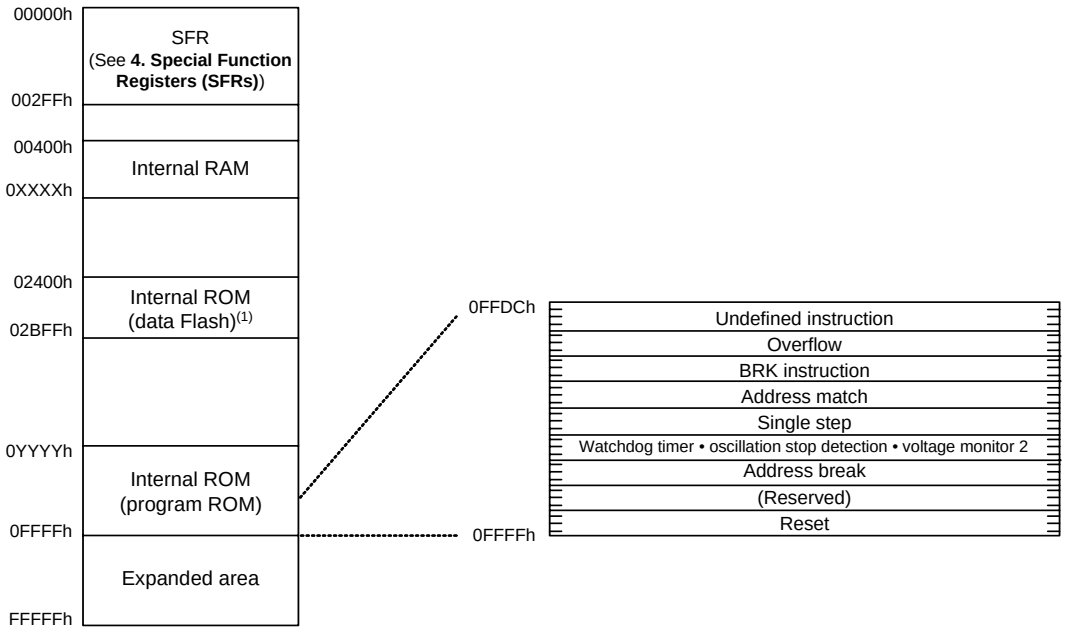
Figure 1.3 Type Number, Memory Size, and Package of R8C/1B Group

Table 1.6 Pin Name Information by Pin Number of PLSP0020JB-A, PRDP0020BA-A Packages

Pin Number	Control Pin	Port	I/O Pin Functions for Peripheral Modules					
			Interrupt	Timer	Serial Interface	Clock Synchronous Serial I/O with Chip Select	I^2C bus Interface	A/D Converter
1		P3_5		CMP1_2		SSCK	SCL	
2		P3_7		$\overline{\text{CNTR0}}$	TXD1	SSO		
3	$\overline{\text{RESET}}$							
4	XOUT	P4_7						
5	VSS/AVSS							
6	XIN	P4_6						
7	VCC/AVCC							
8	MODE							
9		P4_5	$\overline{\text{INT0}}$		RXD1			
10		P1_7	$\overline{\text{INT10}}$	CNTR00				
11		P1_6			CLK0	SSI01		
12		P1_5	$\overline{\text{INT11}}$	CNTR01	RXD0			
13		P1_4			TXD0			
14		P1_3	$\overline{\text{KI3}}$	TZOUT				AN11
15		P1_2	$\overline{\text{KI2}}$	CMP0_2				AN10
16	VREF	P4_2						
17		P1_1	$\overline{\text{KI1}}$	CMP0_1				AN9
18		P1_0	$\overline{\text{KI0}}$	CMP0_0				AN8
19		P3_3	$\overline{\text{INT3}}$	TCIN/ CMP1_0		SSI00		
20		P3_4		CMP1_1		$\overline{\text{SCS}}$	SDA	

3.2 R8C/1B Group

Figure 3.2 is a Memory Map of R8C/1B Group. The R8C/1B Group has 1 Mbyte of address space from addresses 00000h to FFFFFh.
The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal ROM (data flash) is allocated addresses 02400h to 02BFFh.
The internal RAM is allocated higher addresses beginning with address 00400h. For example, a 1-Kbyte internal RAM area is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



NOTES:
1. Data flash block A (1 Kbyte) and B (1 Kbyte) are shown.
2. The blank regions are reserved. Do not access locations in these regions.

Part Number	Internal ROM		Internal RAM	
	Size	Address 0YYYYh	Size	Address 0XXXXh
R5F211B4SP, R5F211B4DSP, R5F211B4DD, R5F211B4NP, R5F211B4XXXSP, R5F211B4DXXXSP, R5F211B4XXXDD, R5F211B4XXXNP	16 Kbytes	0C000h	1 Kbyte	007FFh
R5F211B3SP, R5F211B3DSP, R5F211B3DD, R5F211B3NP, R5F211B3XXXSP, R5F211B3DXXXSP, R5F211B3XXXDD, R5F211B3XXXNP	12 Kbytes	0D000h	768 bytes	006FFh
R5F211B2SP, R5F211B2DSP, R5F211B2DD, R5F211B2NP, R5F211B2XXXSP, R5F211B2DXXXSP, R5F211B2XXXDD, R5F211B2XXXNP	8 Kbytes	0E000h	512 bytes	005FFh
R5F211B1SP, R5F211B1DSP, R5F211B1DD, R5F211B1XXXSP, R5F211B1DXXXSP, R5F211B1XXXDD	4 Kbytes	0F000h	384 bytes	0057Fh

Figure 3.2 Memory Map of R8C/1B Group

Table 4.2 SFR Information (2)[1]

Address	Register	Symbol	After reset
0040h			
0041h			
0042h			
0043h			
0044h			
0045h			
0046h			
0047h			
0048h			
0049h			
004Ah			
004Bh			
004Ch			
004Dh	Key Input Interrupt Control Register	KUPIC	XXXXX000b
004Eh	A/D Conversion Interrupt Control Register	ADIC	XXXXX000b
004Fh	SSU/IIC Interrupt Control Register[2]	SSUAIC/IIC2AIC	XXXXX000b
0050h	Compare 1 Interrupt Control Register	CMP1IC	XXXXX000b
0051h	UART0 Transmit Interrupt Control Register	S0TIC	XXXXX000b
0052h	UART0 Receive Interrupt Control Register	S0RIC	XXXXX000b
0053h	UART1 Transmit Interrupt Control Register	S1TIC	XXXXX000b
0054h	UART1 Receive Interrupt Control Register	S1RIC	XXXXX000b
0055h			
0056h	Timer X Interrupt Control Register	TXIC	XXXXX000b
0057h			
0058h	Timer Z Interrupt Control Register	TZIC	XXXXX000b
0059h	INT1 Interrupt Control Register	INT1IC	XXXXX000b
005Ah	INT3 Interrupt Control Register	INT3IC	XXXXX000b
005Bh	Timer C Interrupt Control Register	TCIC	XXXXX000b
005Ch	Compare 0 Interrupt Control Register	CMP0IC	XXXXX000b
005Dh	INT0 Interrupt Control Register	INT0IC	XX00X000b
005Eh			
005Fh			
0060h			
0061h			
0062h			
0063h			
0064h			
0065h			
0066h			
0067h			
0068h			
0069h			
006Ah			
006Bh			
006Ch			
006Dh			
006Eh			
006Fh			
0070h			
0071h			
0072h			
0073h			
0074h			
0075h			
0076h			
0077h			
0078h			
0079h			
007Ah			
007Bh			
007Ch			
007Dh			
007Eh			
007Fh			

X: Undefined

NOTES:

1. The blank regions are reserved. Do not access locations in these regions.
2. Selected by the IICSEL bit in the PMR register.

Table 4.3 SFR Information (3)(1)

Address	Register	Symbol	After reset
0080h	Timer Z Mode Register	TZMR	00h
0081h			
0082h			
0083h			
0084h	Timer Z Waveform Output Control Register	PUM	00h
0085h	Prescaler Z Register	PREZ	FFh
0086h	Timer Z Secondary Register	TZSC	FFh
0087h	Timer Z Primary Register	TZPR	FFh
0088h			
0089h			
008Ah	Timer Z Output Control Register	TZOC	00h
008Bh	Timer X Mode Register	TXMR	00h
008Ch	Prescaler X Register	PREX	FFh
008Dh	Timer X Register	TX	FFh
008Eh	Timer Count Source Setting Register	TCSS	00h
008Fh			
0090h	Timer C Register	TC	00h
0091h			00h
0092h			
0093h			
0094h			
0095h			
0096h	External Input Enable Register	INTEN	00h
0097h			
0098h	Key Input Enable Register	KIEN	00h
0099h			
009Ah	Timer C Control Register 0	TCC0	00h
009Bh	Timer C Control Register 1	TCC1	00h
009Ch	Capture, Compare 0 Register	TM0	0000h(2)
009Dh			FFFFh(3)
009Eh	Compare 1 Register	TM1	FFh
009Fh			FFh
00A0h	UART0 Transmit/Receive Mode Register	U0MR	00h
00A1h	UART0 Bit Rate Generator	U0BRG	XXh
00A2h	UART0 Transmit Buffer Register	U0TB	XXh
00A3h			XXh
00A4h	UART0 Transmit/Receive Control Register 0	U0C0	00001000b
00A5h	UART0 Transmit/Receive Control Register 1	U0C1	00000010b
00A6h	UART0 Receive Buffer Register	U0RB	XXh
00A7h			XXh
00A8h	UART1 Transmit/Receive Mode Register	U1MR	00h
00A9h	UART1 Bit Rate Generator	U1BRG	XXh
00AAh	UART1 Transmit Buffer Register	U1TB	XXh
00ABh			XXh
00ACh	UART1 Transmit/Receive Control Register 0	U1C0	00001000b
00ADh	UART1 Transmit/Receive Control Register 1	U1C1	00000010b
00AEh	UART1 Receive Buffer Register	U1RB	XXh
00AFh			XXh
00B0h	UART Transmit/Receive Control Register 2	UCON	00h
00B1h			
00B2h			
00B3h			
00B4h			
00B5h			
00B6h			
00B7h			
00B8h	SS Control Register H / IIC bus Control Register 1(4)	SSCRH / ICCR1	00h
00B9h	SS Control Register L / IIC bus Control Register 2(4)	SSCRL / ICCR2	01111101b
00BAh	SS Mode Register / IIC bus Mode Register(4)	SSMR / ICMR	00011000b
00BBh	SS Enable Register / IIC bus Interrupt Enable Register(4)	SSER / ICIER	00h
00BCh	SS Status Register / IIC bus Status Register(4)	SSSR / ICSR	00h / 0000X000b
00BDh	SS Mode Register 2 / Slave Address Register(4)	SSMR2 / SAR	00h
00BEh	SS Transmit Data Register / IIC bus Transmit Data Register(4)	SSTDR / ICDRT	FFh
00BFh	SS Receive Data Register / IIC bus Receive Data Register(4)	SSRDR / ICDRR	FFh

X: Undefined

NOTES:

1. The blank regions are reserved. Do not access locations in these regions.
2. In input capture mode.
3. In output compare mode.
4. Selected by the IICSEL bit in the PMR register.

Table 5.4 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)	R8C/1A Group	100(3)	–	–	times
		R8C/1B Group	1,000(3)	–	–	times
–	Byte program time		–	50	400	µs
–	Block erase time		–	0.4	9	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97+CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3+CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time(8)	Ambient temperature = 55 °C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = 0 to 60 °C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. If emergency processing is required, a suspend request can be generated independent of this characteristic. In that case the normal time delay to suspend can be applied to the request. However, we recommend that a suspend request with an interval of less than 650 µs is only used once because, if the suspend state continues, erasure cannot operate and the incidence of erasure error rises.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the number of erase operations between block A and block B can further reduce the effective number of rewrites. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring programming/erasure failure rate information should contact their Renesas technical support representative.
8. The data hold time includes time that the power supply is off or the clock is not supplied.

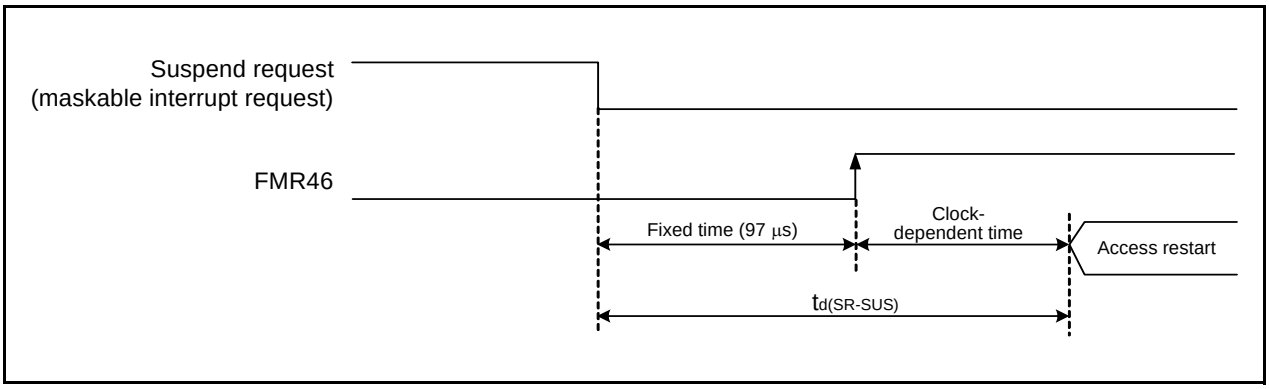


Figure 5.2 Transition Time to Suspend

Table 5.6 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level(3)		2.70	2.85	3.00	V
–	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	–	600	–	nA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(2)		–	–	100	µs
Vccmin	MCU operating voltage minimum value		2.7	–	–	V

NOTES:
1. The measurement condition is V_{CC} = 2.7 V to 5.5 V and T_{opr} = -40°C to 85 °C.
2. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.
3. Ensure that $V_{det2} > V_{det1}$.

Table 5.7 Voltage Detection 2 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level(4)		3.00	3.30	3.60	V
–	Voltage monitor 2 interrupt request generation time(2)		–	40	–	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0 V	–	600	–	nA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.7 V to 5.5 V and T_{opr} = -40°C to 85 °C.
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det2}.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.
4. Ensure that $V_{det2} > V_{det1}$.

Table 5.8 Reset Circuit Electrical Characteristics (When Using Voltage Monitor 1 Reset)

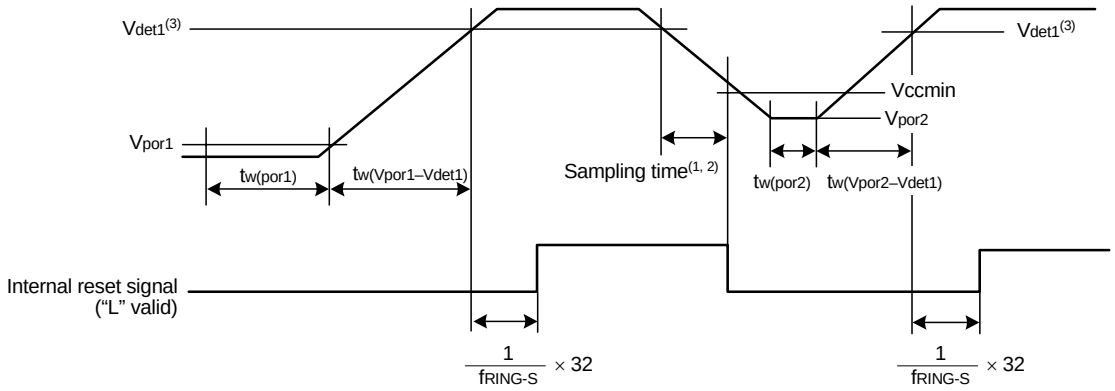
Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{por2}	Power-on reset valid voltage	-20°C ≤ Topr ≤ 85°C	–	–	V_{det1}	V
$t_{w(Vpor2-Vdet1)}$	Supply voltage rising time when power-on reset is deasserted(1)	-20°C ≤ Topr ≤ 85°C, $t_{w(por2)}$ ≥ 0s(3)	–	–	100	ms

NOTES:
1. This condition is not applicable when using with Vcc ≥ 1.0 V.
2. When turning power on after the time to hold the external power below effective voltage (V_{por1}) exceeds10 s, refer to **Table 5.9 Reset Circuit Electrical Characteristics (When Not Using Voltage Monitor 1 Reset)**.
3. $t_{w(por2)}$ is the time to hold the external power below effective voltage (V_{por2}).

Table 5.9 Reset Circuit Electrical Characteristics (When Not Using Voltage Monitor 1 Reset)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{por1}	Power-on reset valid voltage	-20°C ≤ Topr ≤ 85°C	–	–	0.1	V
$t_{w(Vpor1-Vdet1)}$	Supply voltage rising time when power-on reset is deasserted	0°C ≤ Topr ≤ 85°C, $t_{w(por1)}$ ≥ 10 s(2)	–	–	100	ms
$t_{w(Vpor1-Vdet1)}$	Supply voltage rising time when power-on reset is deasserted	-20°C ≤ Topr < 0°C, $t_{w(por1)}$ ≥ 30 s(2)	–	–	100	ms
$t_{w(Vpor1-Vdet1)}$	Supply voltage rising time when power-on reset is deasserted	-20°C ≤ Topr < 0°C, $t_{w(por1)}$ ≥ 10 s(2)	–	–	1	ms
$t_{w(Vpor1-Vdet1)}$	Supply voltage rising time when power-on reset is deasserted	0°C ≤ Topr ≤ 85°C, $t_{w(por1)}$ ≥ 1 s(2)	–	–	0.5	ms

NOTES:
1. When not using voltage monitor 1, use with Vcc≥ 2.7 V.
2. $t_{w(por1)}$ is the time to hold the external power below effective voltage (V_{por1}).



NOTES:
1. Hold the voltage inside the MCU operation voltage range (Vccmin or above) within the sampling time.
2. The sampling clock can be selected. Refer to **7. Voltage Detection Circuit** for details.
3. V_{det1} indicates the voltage detection level of the voltage detection 1 circuit. Refer to **7. Voltage Detection Circuit** for details.

Figure 5.3 Reset Circuit Electrical Characteristics

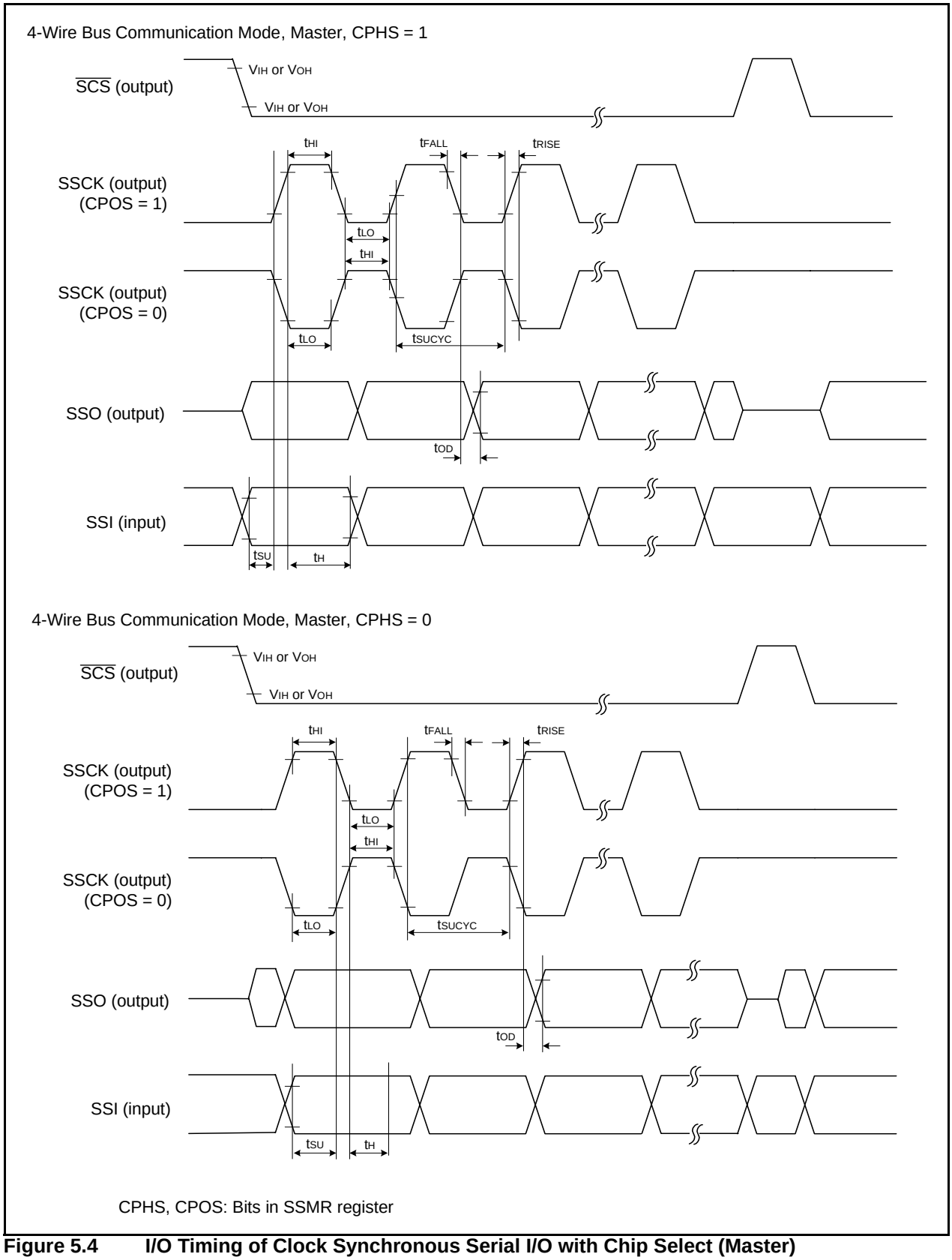


Figure 5.4 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Master)

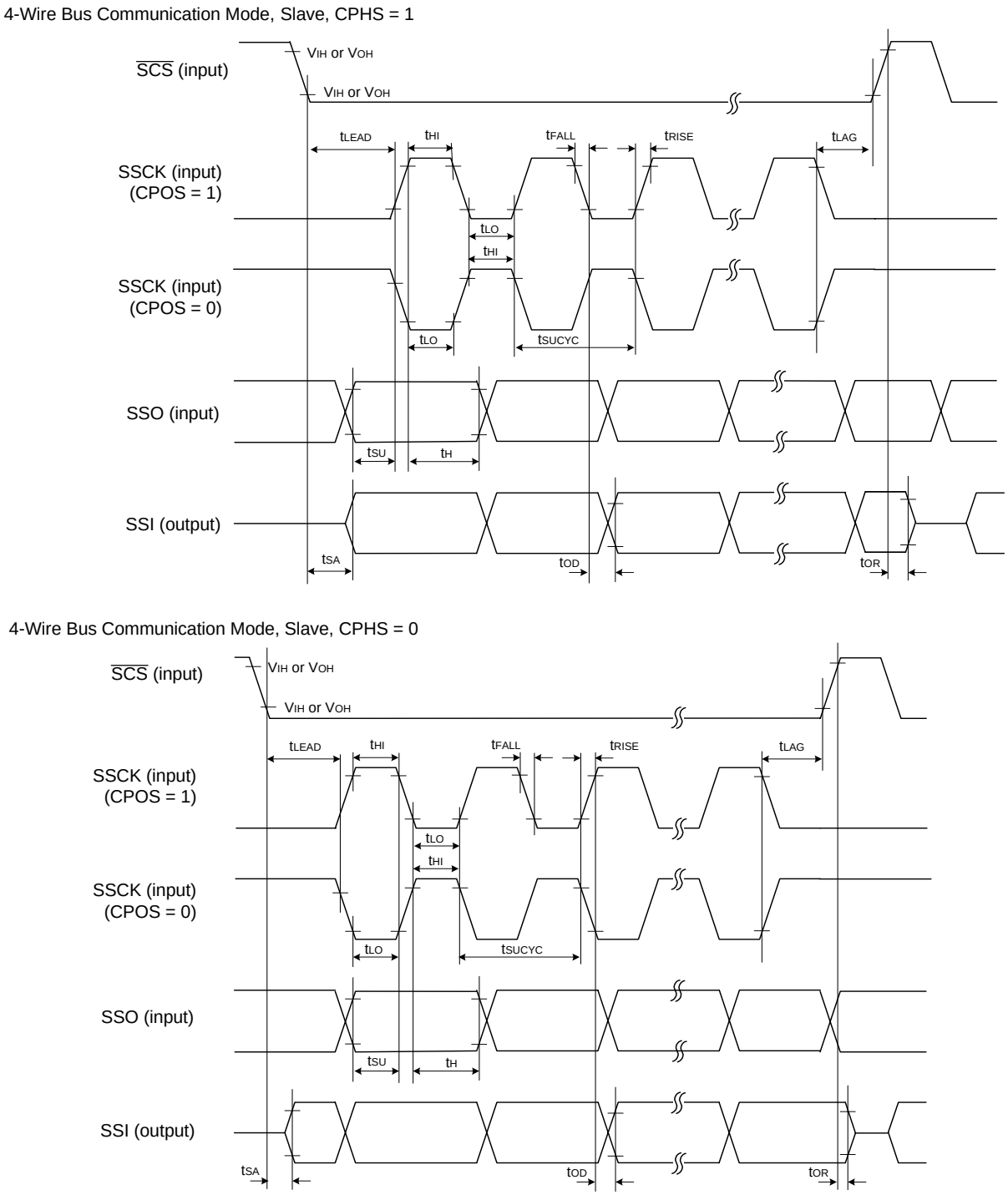


Figure 5.5 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Slave)

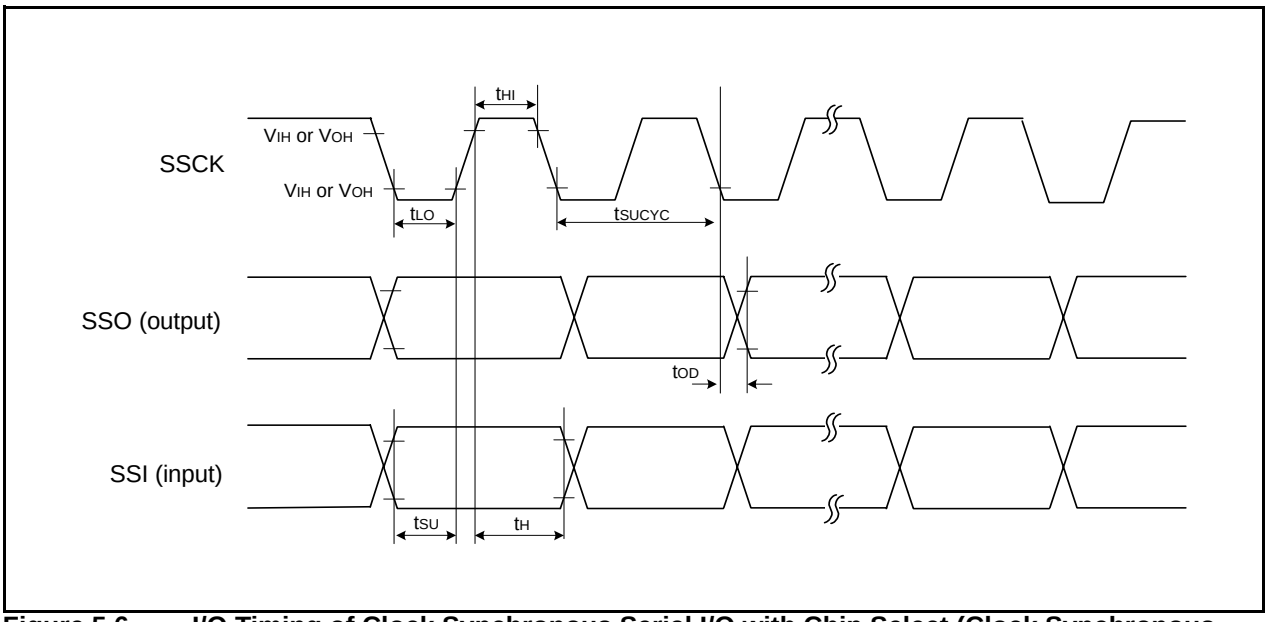


Figure 5.6 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Clock Synchronous Communication Mode)

Table 5.14 Electrical Characteristics (1) [V_{CC} = 5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except X_{OUT}	I_{OH} = -5 mA		V_{CC} – 2.0	–	V_{CC}	V
			I_{OH} = -200 µA		V_{CC} – 0.3	–	V_{CC}	V
		X_{OUT}	Drive capacity HIGH	I_{OH} = -1 mA	V_{CC} – 2.0	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -500 µA	V_{CC} – 2.0	–	V_{CC}	V
V_{OL}	Output “L” voltage	Except P1_0 to P1_3, X_{OUT}	I_{OL} = 5 mA		–	–	2.0	V
			I_{OL} = 200 µA		–	–	0.45	V
		P1_0 to P1_3	Drive capacity HIGH	I_{OL} = 15 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 5 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 200 µA	–	–	0.45	V
		X_{OUT}	Drive capacity HIGH	I_{OL} = 1 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 500 µA	–	–	2.0	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, CNTR0, CNTR1, TCIN, RXD0			0.2	–	1.0	V
		$\overline{RESET}$			0.2	–	2.2	V
I_{IH}	Input “H” current		VI = 5 V		–	–	5.0	µA
I_{IL}	Input “L” current		VI = 0 V		–	–	-5.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V		30	50	167	kΩ
R_{fXIN}	Feedback resistance	XIN			–	1.0	–	MΩ
f_{RING-S}	Low-speed on-chip oscillator frequency				40	125	250	kHz
V_{RAM}	RAM hold voltage		During stop mode		2.0	–	–	V

NOTE:
1. V_{CC} = 4.2 to 5.5 V at T_{opr} = -20 to 85 °C / -40 to 85 °C, f(XIN) = 20 MHz, unless otherwise specified.

Table 5.15 Electrical Characteristics (2) [Vcc = 5 V] (Topr = -40 to 85 °C, unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
I_{CC}	Power supply current (V_{CC} = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are V_{SS}, A/D converter is stopped	High-speed mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	9	15	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	8	14	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	5	–	mA
		Medium-speed mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	4	–	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2	–	mA
		High-speed on-chip oscillator mode	Main clock off High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	4	8	mA
			Main clock off High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		Low-speed on-chip oscillator mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8 FMR47 = 1	–	110	300	µA
		Wait mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = 0	–	40	80	µA
		Wait mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = 0	–	38	76	µA
		Stop mode	Main clock off, Topr = 25 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = 0	–	0.8	3.0	µA

Table 5.19 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	200	–	ns
$t_{W(CKH)}$	CLKi input “H” width	100	–	ns
$t_{W(CKL)}$	CLKi input “L” width	100	–	ns
$t_{d(C-Q)}$	TXDi output delay time	–	50	ns
$t_{h(C-Q)}$	TXDi hold time	0	–	ns
$t_{su(D-C)}$	RXDi input setup time	50	–	ns
$t_{h(C-D)}$	RXDi input hold time	90	–	ns

i = 0 or 1

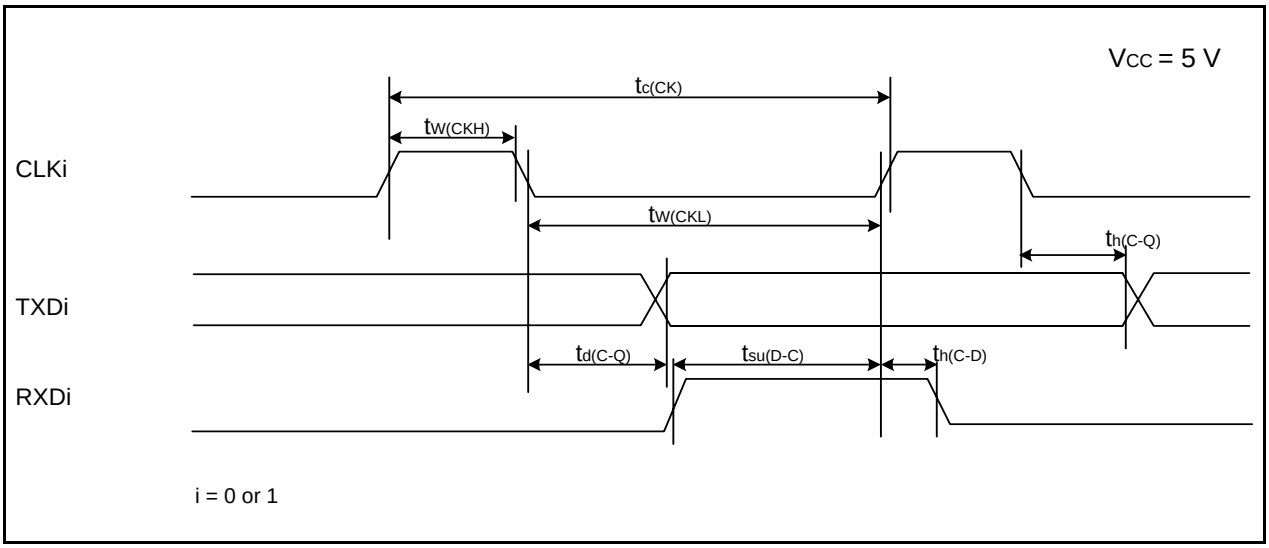


Figure 5.11 Serial Interface Timing Diagram when Vcc = 5 V

Table 5.20 External Interrupt $\overline{INT0}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INT0}$ input “H” width	250(1)	–	ns
$t_{W(INL)}$	$\overline{INT0}$ input “L” width	250(2)	–	ns

NOTES:
1. When selecting the digital filter by the $\overline{INT0}$ input filter select bit, use an $\overline{INT0}$ input HIGH width of either (1/digital filter clock frequency x 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INT0}$ input filter select bit, use an $\overline{INT0}$ input LOW width of either (1/digital filter clock frequency x 3) or the minimum value of standard, whichever is greater.

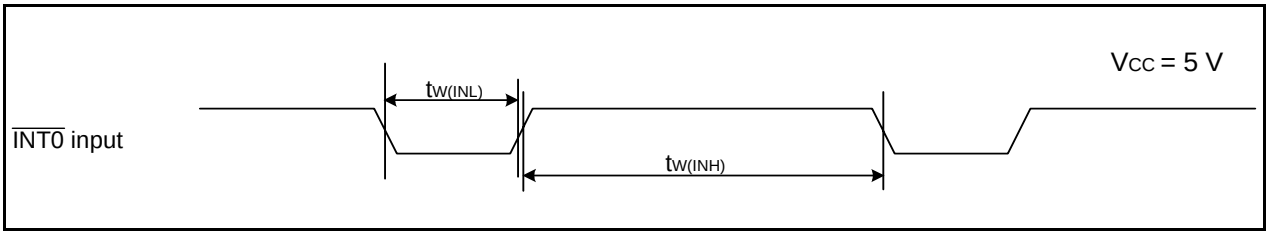


Figure 5.12 External Interrupt $\overline{INT0}$ Input Timing Diagram when Vcc = 5 V

Table 5.22 Electrical Characteristics (4) [Vcc = 3 V] (Topr = -40 to 85 °C, unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
I_{CC}	Power supply current (V_{CC} = 2.7 to 3.3 V) Single-chip mode, output pins are open, other pins are V_{SS}, A/D converter is stopped	High-speed mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	8	13	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	7	12	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	5	–	mA
		Medium-speed mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3	–	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.5	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.6	–	mA
		High-speed on-chip oscillator mode	Main clock off High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	3.5	7.5	mA
			Main clock off High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		Low-speed on-chip oscillator mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8 FMR47 = 1	–	100	280	µA
		Wait mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = 0	–	37	74	µA
		Wait mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = 0	–	35	70	µA
		Stop mode	Main clock off, Topr = 25 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = 0	–	0.7	3.0	µA

REVISION HISTORY	R8C/1A Group, R8C/1B Group Datasheet

Rev.	Date	Description	
		Page	Summary
0.10	Feb 18, 2005	–	First Edition issued
0.20	Jun 01, 2005	2, 3	Tables 1.1, 1.2: Item name changed
		9	Table 1.5: Timer C's Pin name revised, Reference Voltage Input Description revised
0.30	Jul 04, 2005	16	Table 4.1 the value after reset revised; 0009h address "XXXXXX00b" → "00h", 000Ah address "00XXX000b" → "00h", 001Eh address "XXXXX000b" → "00h".
		17	Table 4.2 004Fh address; "SSU/IIC Interrupt Control Register, SSUAIC/IIC2AIC, XXXXX000b" added
		18	Table 4.3 the value after reset revised; 00BCh address "00h" → "00h / 0000X000b"
		20 to 39	5. Electrical Characteristics added
1.00	Sep 01, 2005	all pages	"Under development" deleted
		3	Table 1.2 Performance Outline of the R8C/1B Group; Flash Memory: (Data area) → (Data flash) (Program area) → (Program ROM) revised
		4	Figure 1.1 Block Diagram; "Peripheral Function" added, "System Clock Generation" → "System Clock Generator" revised
		5	Table 1.3 Product Information of R8C/1A Group; "(D)" and "(D): Under development" deleted
		6	Table 1.4 Product Information of R8C/1B Group; "(D)" and "(D): Under development" deleted ROM capacity: (Program area) → (Program ROM), (Data area) → (Data flash) revised
		9	Table 1.5 Pin Description; Power Supply Input: "VCC/AVCC" → "VCC", "VSS/AVSS" → "VSS" revised Analog Power Supply Input: added
		11	Figure 2.1 CPU Register; "Reserved Area" → "Reserved Bit" revised
		13	2.8.10 Reserved Area; "Reserved Area" → "Reserved Bit" revised
		15	3.2 R8C/1B Group, Figure 3.2 Memory Map of R8C/1B Group; "Data area" → "Data flash", "Program area" → "Program ROM" revised

REVISION HISTORY	R8C/1A Group, R8C/1B Group Datasheet

Rev.	Date	Description	
		Page	Summary
1.30	Oct 03, 2006	1	1.1 “portable equipment” added
		2, 3	Table 1.1, Table 1.2; Specification Interrupts: “Internal: 9 sources” → “Internal: 11 sources”
		24	Table 5.2; Parameter: System clock added
		45	Package Dimensions; PWQN0028KA-B revised
1.40	Dec 08, 2006	20	Table 4.1; 000Fh: After reset “000XXXXXb” → “00X11111b”
		24	Table 19.2; Parameter: OCD2 = 1 On-chip oscillator clock selected revised

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